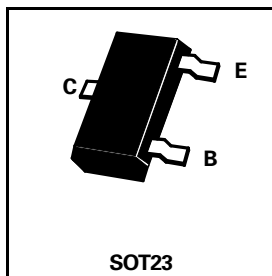


# SOT23 PNP SILICON PLANAR SWITCHING TRANSISTORS

ISSUE 2 – SEPTEMBER 95

## BSS80B BSS80C

PARTMARKING DETAIL — BSS80B - CH  
BSS80C - CJ



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-800	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{TOT}$	330	mW
Operating and Storage Temperature Range	$t_j:t_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER		SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	-60		V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	-40		V	$I_C = -10mA$
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-5			$I_E = -10mA$
Collector Cut-Off Current		$I_{CBO}$		-10 -10	nA $\mu A$	$V_{CB} = -50V, V_{CE} = -50V, T_a = 150^{\circ}C$
Emitter Cut-Off Current		$I_{EBO}$		-10	nA	$V_{BE} = -3V$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$		-0.4 -1.6	mV V	$I_C = -150mA, V_{CE} = -10V$ $I_C = -150mA, V_{CE} = -10V$
Static Forward Current Transfer Ratio	BSS80B BSS80C	$h_{FE}$	40 100	120 300		$I_C = 150mA, V_{CE} = 10V$ $I_C = 150mA, V_{CE} = 10V$
Transition Frequency		$f_T$	200		MHz	$V_{CE} = -20V, I_C = -50mA$ $f = 100MHz$
Output Capacitance		$C_{obo}$		8	pF	$V_{CB} = -10V, f = 1MHz$
Delay Time		$t_d$		10	ns	$V_{CC} = -30V, I_C = -150mA$ $I_{B1} = -I_{B2} = -15mA$
Rise Time		$t_r$		40	ns	
Storage Time		$t_s$		80	ns	
Fall Time		$t_f$		30	ns	